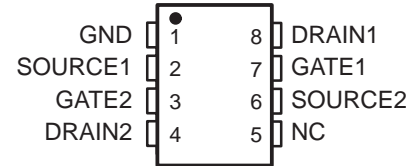


TPIC5223L 2-CHANNEL INDEPENDENT GATE-PROTECTED LOGIC-LEVEL POWER DMOS ARRAY

SLIS043A – NOVEMBER 1994 – REVISED SEPTEMBER 1995

- Low $r_{DS(on)}$. . . 0.38 Ω Typ
- Voltage Output . . . 60 V
- Input Protection Circuitry . . . 18 V
- Pulsed Current . . . 3 A Per Channel
- Extended ESD Capability . . . 4000 V
- Direct Logic-Level Interface

**D PACKAGE
(TOP VIEW)**



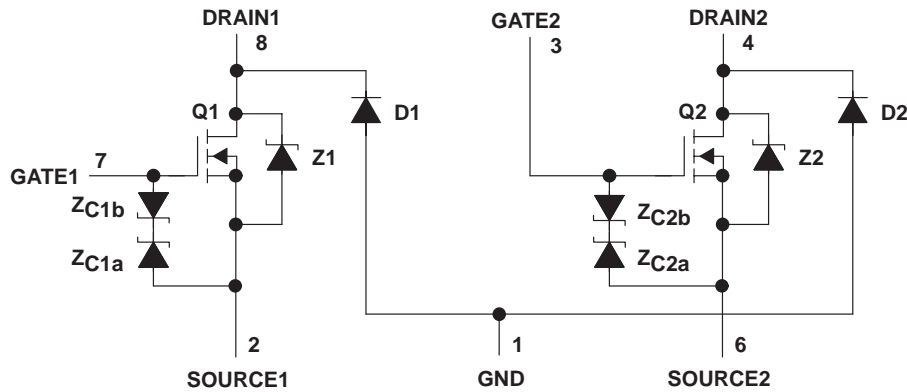
NC – No internal connection

description

The TPIC5223L is a monolithic gate-protected logic-level power DMOS array that consists of two electrically isolated independent N-channel enhancement-mode DMOS transistors. Each transistor features integrated high-current zener diodes (Z_{CXa} and Z_{CXb}) to prevent gate damage in the event that an overstress condition occurs. These zener diodes also provide up to 4000 V of ESD protection when tested using the human-body model of a 100-pF capacitor in series with a 1.5-k Ω resistor.

The TPIC5223L is offered in a standard eight-pin small-outline surface-mount (D) package and is characterized for operation over the case temperature of -40°C to 125°C .

schematic



NOTE A: For correct operation, no terminal may be taken below GND.

TPIC5223L

2-CHANNEL INDEPENDENT GATE-PROTECTED LOGIC-LEVEL

POWER DMOS ARRAY

SLIS043A – NOVEMBER 1994 – REVISED SEPTEMBER 1995

absolute maximum ratings over operating case temperature range (unless otherwise noted)[†]

Drain-to-source voltage, V_{DS}	60 V
Source-to-GND voltage	100 V
Drain-to-GND voltage	100 V
Gate-to-source voltage range, V_{GS}	–9 V to 18 V
Continuous drain current, each output, $T_C = 25^\circ\text{C}$	1 A
Continuous source-to-drain diode current, $T_C = 25^\circ\text{C}$	1 A
Pulsed drain current, each output, I_{max} , $T_C = 25^\circ\text{C}$ (see Note 1 and Figure 15)	3 A
Continuous gate-to-source zener diode current, $T_C = 25^\circ\text{C}$	± 50 mA
Pulsed gate-to-source zener-diode current, $T_C = 25^\circ\text{C}$	± 500 mA
Single-pulse avalanche energy, E_{AS} , $T_C = 25^\circ\text{C}$ (see Figures 4 and 16)	108 mJ
Continuous total power dissipation, $T_C = 25^\circ\text{C}$ (see Figure 15)	0.95 W
Operating virtual junction temperature range, T_J	–40°C to 150°C
Operating case temperature range, T_C	–40°C to 125°C
Storage temperature range, T_{stg}	–65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

[†] Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: Pulse duration = 10 ms, duty cycle = 2%



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TPIC5223L
2-CHANNEL INDEPENDENT GATE-PROTECTED LOGIC-LEVEL
POWER DMOS ARRAY

SLIS043A – NOVEMBER 1994 – REVISED SEPTEMBER 1995

electrical characteristics, $T_C = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
$V_{(BR)DSX}$	Drain-to-source breakdown voltage	$I_D = 250\ \mu\text{A}$,	$V_{GS} = 0$	60			V
$V_{GS(th)}$	Gate-to-source threshold voltage	$I_D = 1\ \text{mA}$, See Figure 5	$V_{DS} = V_{GS}$,	1.5	2.05	2.2	V
$V_{(BR)GS}$	Gate-to-source breakdown voltage	$I_{GS} = 250\ \mu\text{A}$		18			V
$V_{(BR)SG}$	Source-to-gate breakdown voltage	$I_{SG} = 250\ \mu\text{A}$		9			V
$V_{(BR)}$	Reverse drain-to-GND breakdown voltage (across D1, D2)	Drain-to-GND current = $250\ \mu\text{A}$		100			V
$V_{DS(on)}$	Drain-to-source on-state voltage	$I_D = 1\ \text{A}$, See Notes 2 and 3	$V_{GS} = 5\ \text{V}$,		0.375	0.425	V
$V_{F(SD)}$	Forward on-state voltage, source-to-drain	$I_S = 1\ \text{A}$, $V_{GS} = 0$ (Z1, Z2), See Notes 2 and 3 and Figure 12			0.85	1.2	V
V_F	Forward on-state voltage, GND-to-drain	$I_D = 1\ \text{A}$ (D1, D2), See Notes 2 and 3			3		V
I_{DSS}	Zero-gate-voltage drain current	$V_{DS} = 48\ \text{V}$, $V_{GS} = 0$	$T_C = 25^\circ\text{C}$		0.05	1	μA
			$T_C = 125^\circ\text{C}$		0.5	10	
I_{GSSF}	Forward-gate current, drain short circuited to source	$V_{GS} = 15\ \text{V}$,	$V_{DS} = 0$		20	200	nA
I_{GSSR}	Reverse-gate current, drain short circuited to source	$V_{SG} = 5\ \text{V}$,	$V_{DS} = 0$		10	100	nA
I_{lkg}	Leakage current, drain-to-GND	$V_{DGND} = 48\ \text{V}$	$T_C = 25^\circ\text{C}$		0.05	1	μA
			$T_C = 125^\circ\text{C}$		0.5	10	
$r_{DS(on)}$	Static drain-to-source on-state resistance	$V_{GS} = 5\ \text{V}$, $I_D = 1\ \text{A}$, See Notes 2 and 3 and Figures 6 and 7	$T_C = 25^\circ\text{C}$		0.38	0.43	Ω
			$T_C = 125^\circ\text{C}$		0.61	0.65	
g_{fs}	Forward transconductance	$V_{DS} = 15\ \text{V}$, See Notes 2 and 3 and Figure 9	$I_D = 500\ \text{mA}$,	1.2	1.49		S
C_{iss}	Short-circuit input capacitance, common source	$V_{DS} = 25\ \text{V}$, $f = 1\ \text{MHz}$,	$V_{GS} = 0$, See Figure 11		150	190	pF
C_{oss}	Short-circuit output capacitance, common source				100	125	
C_{rss}	Short-circuit reverse transfer capacitance, common source				40	50	

NOTES: 2. Technique should limit $T_J - T_C$ to 10°C maximum.
3. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.

source-to-drain and GND-to-drain diode characteristics, $T_C = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
t_{rr}	Reverse-recovery time	$I_S = 500\ \text{mA}$, $V_{GS} = 0$, See Figures 1 and 14	Z1 and Z2		50		ns
			D1 and D2		210		
Q_{RR}	Total diode charge		Z1 and Z2		50		nC
			D1 and D2		800		



TPIC5223L

2-CHANNEL INDEPENDENT GATE-PROTECTED LOGIC-LEVEL POWER DMOS ARRAY

SLIS043A – NOVEMBER 1994 – REVISED SEPTEMBER 1995

resistive-load switching characteristics, $T_C = 25^\circ\text{C}$

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_{d(on)}$ Turn-on delay time	$V_{DD} = 25\text{ V}$, $R_L = 50\ \Omega$, $t_{r1} = 10\text{ ns}$, $t_{f1} = 10\text{ ns}$, See Figure 2		34	70	ns
$t_{d(off)}$ Turn-off delay time			20	40	
t_{r1} Rise time			28	55	
t_{f2} Fall time			15	30	
Q_g Total gate charge	$V_{DS} = 48\text{ V}$, $I_D = 500\text{ mA}$, $V_{GS} = 5\text{ V}$, See Figure 3		3.1	3.8	nC
$Q_{gs(th)}$ Threshold gate-to-source charge			0.5	0.6	
Q_{gd} Gate-to-drain charge			1.9	2.3	
L_D Internal drain inductance			5		nH
L_S Internal source inductance			5		
R_g Internal gate resistance			0.25		Ω

thermal resistance

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$R_{\theta JA}$ Junction-to-ambient thermal resistance	See Notes 4 and 7		130		$^\circ\text{C/W}$
$R_{\theta JB}$ Junction-to-board thermal resistance	See Notes 5 and 7		78.6		
$R_{\theta JP}$ Junction-to-pin thermal resistance	See Notes 6 and 7		34		

NOTES: 4. Package mounted on an FR4 printed-circuit board with no heatsink.
5. Package mounted on a 24 in², 4-layer FR4 printed-circuit board.
6. Package mounted in intimate contact with infinite heatsink.
7. All outputs with equal power

PARAMETER MEASUREMENT INFORMATION

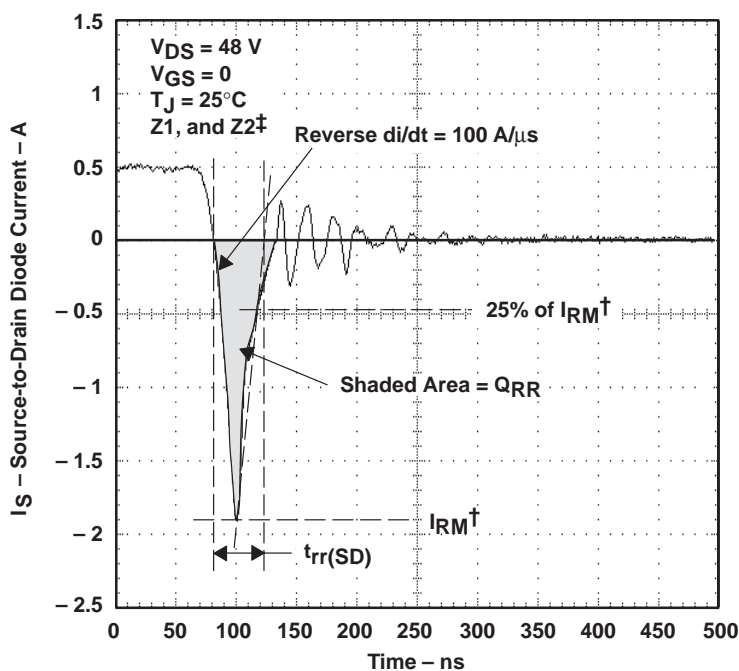
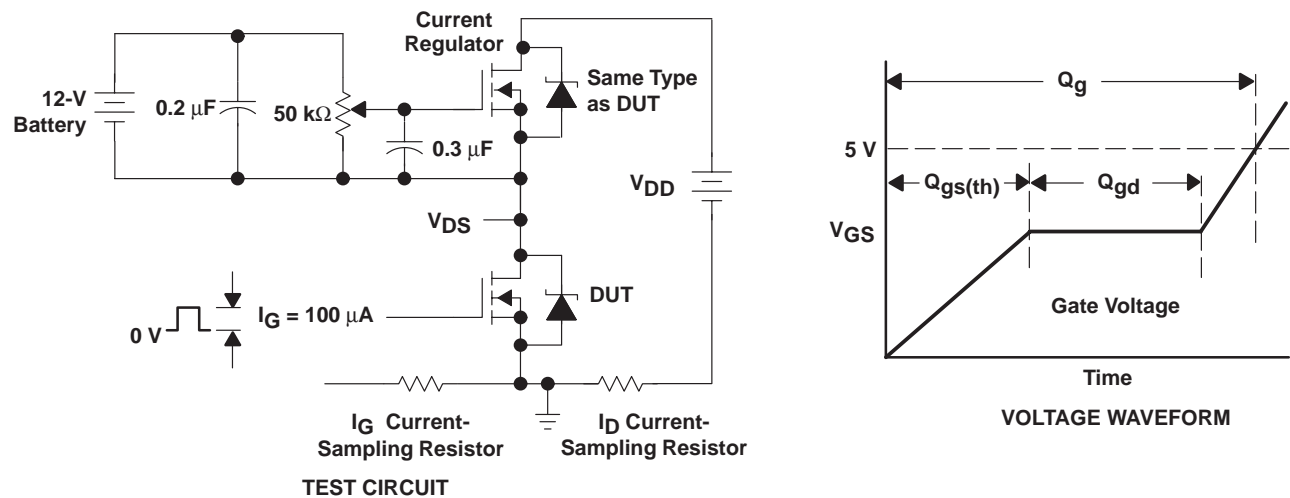
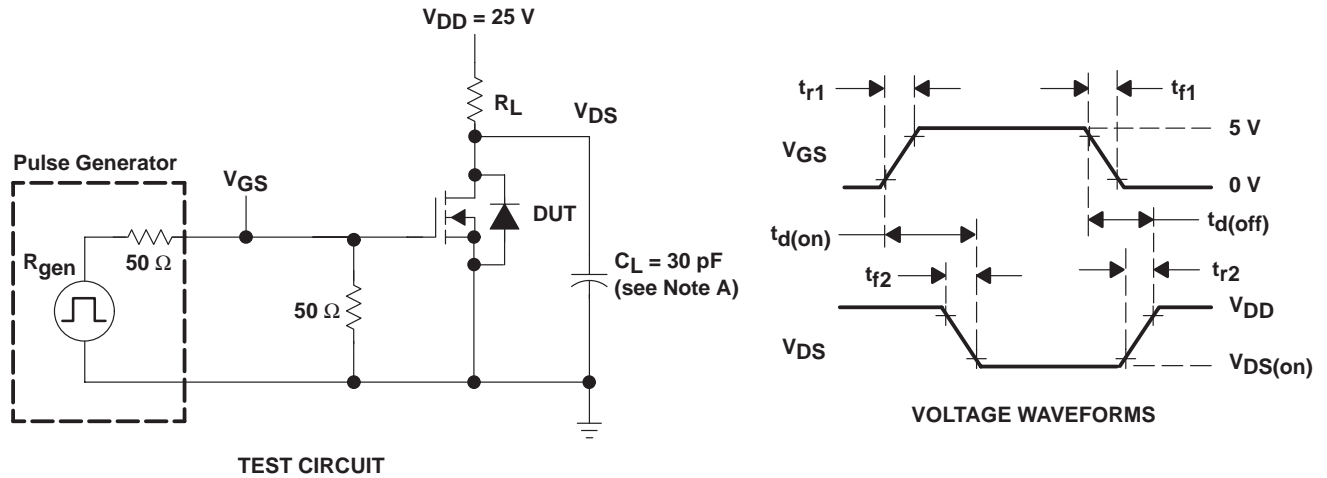


Figure 1. Reverse-Recovery-Current Waveform of Source-to-Drain Diode

PARAMETER MEASUREMENT INFORMATION



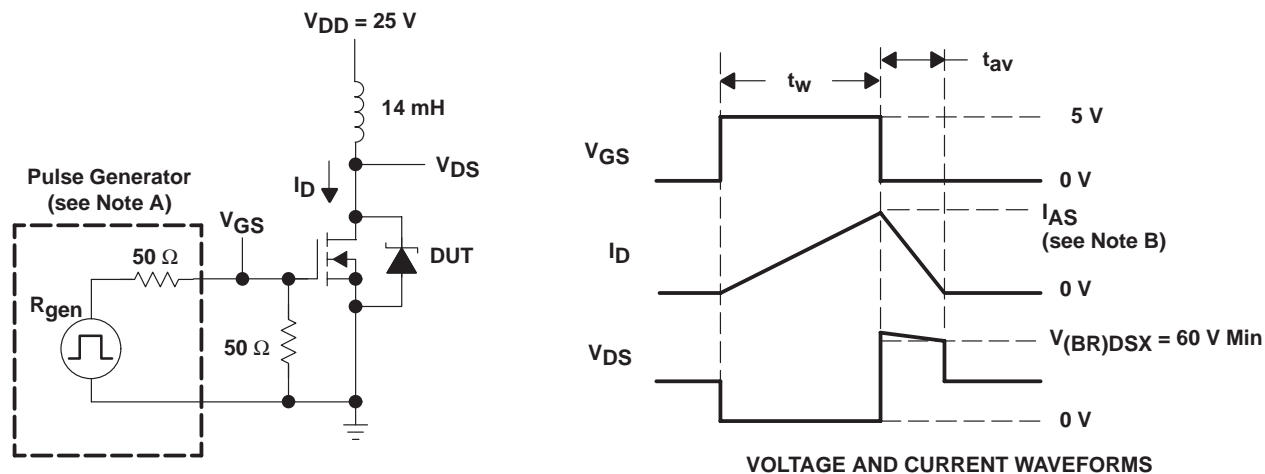
TPIC5223L

2-CHANNEL INDEPENDENT GATE-PROTECTED LOGIC-LEVEL

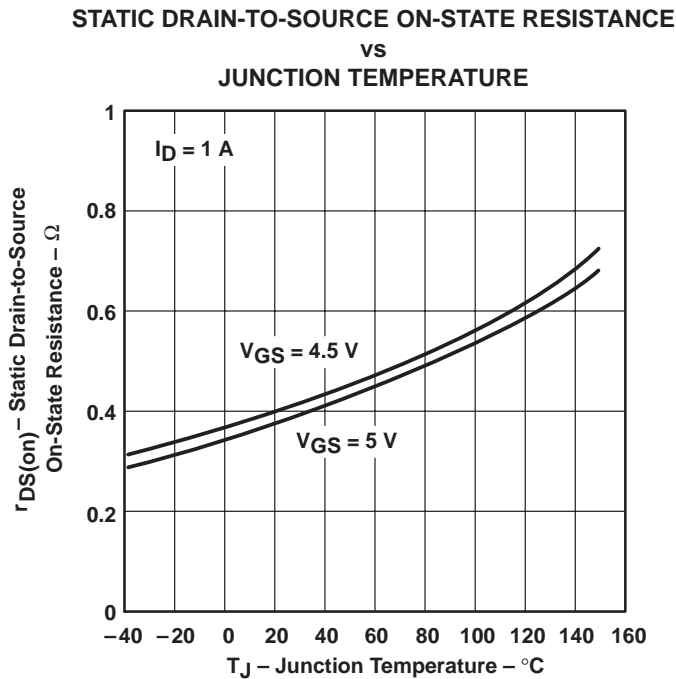
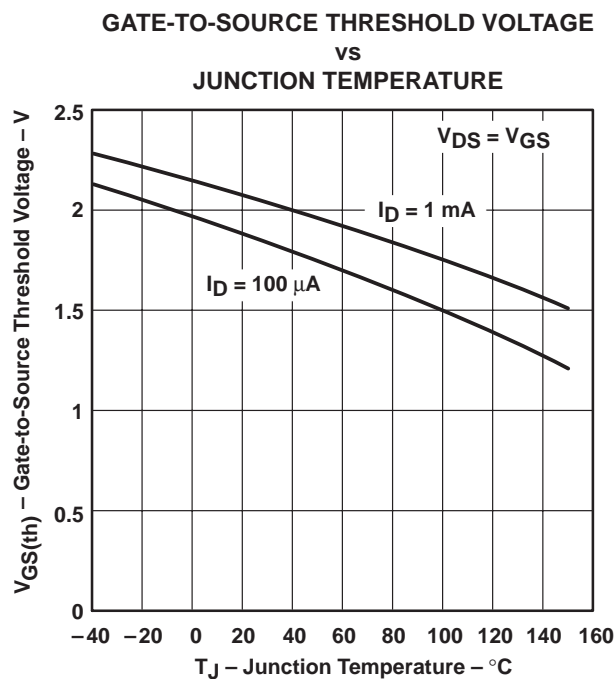
POWER DMOS ARRAY

SLIS043A – NOVEMBER 1994 – REVISED SEPTEMBER 1995

PARAMETER MEASUREMENT INFORMATION



TYPICAL CHARACTERISTICS



TPIC5223L

2-CHANNEL INDEPENDENT GATE-PROTECTED LOGIC-LEVEL POWER DMOS ARRAY

SLIS043A – NOVEMBER 1994 – REVISED SEPTEMBER 1995

TYPICAL CHARACTERISTICS

STATIC DRAIN-TO-SOURCE ON-STATE RESISTANCE
vs
DRAIN CURRENT

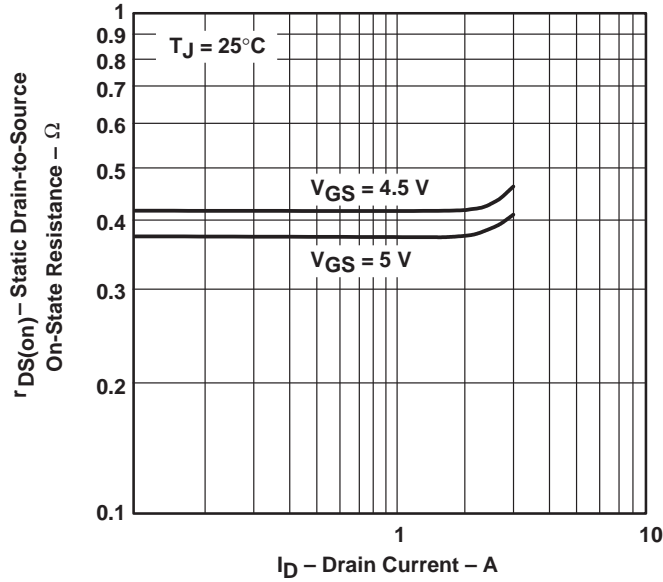


Figure 7

DRAIN CURRENT
vs
DRAIN-TO-SOURCE VOLTAGE

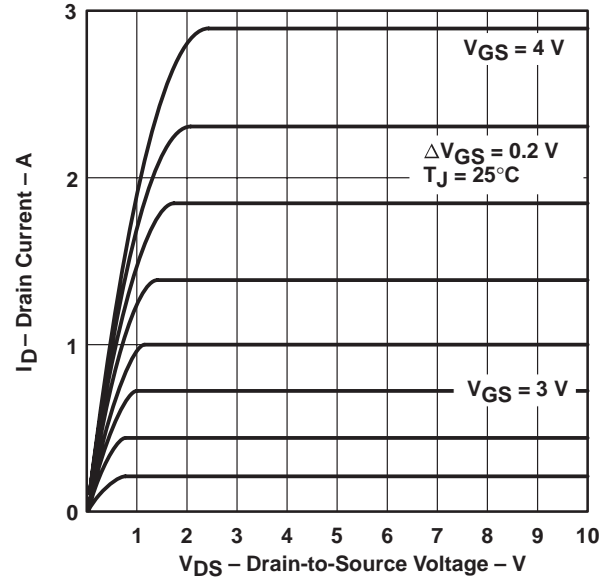


Figure 8

DISTRIBUTION OF
FORWARD TRANSCONDUCTANCE

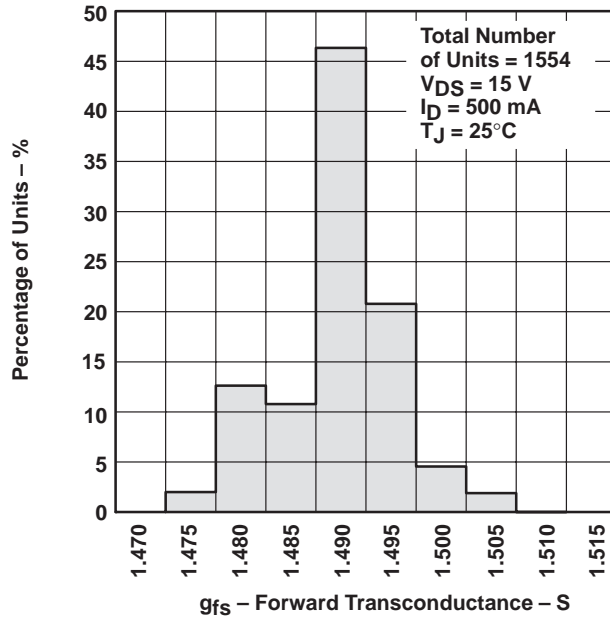


Figure 9

DRAIN CURRENT
vs
GATE-TO-SOURCE VOLTAGE

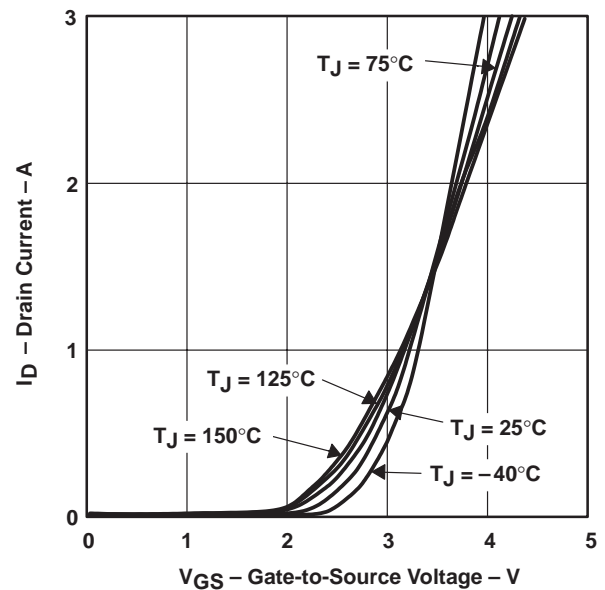


Figure 10

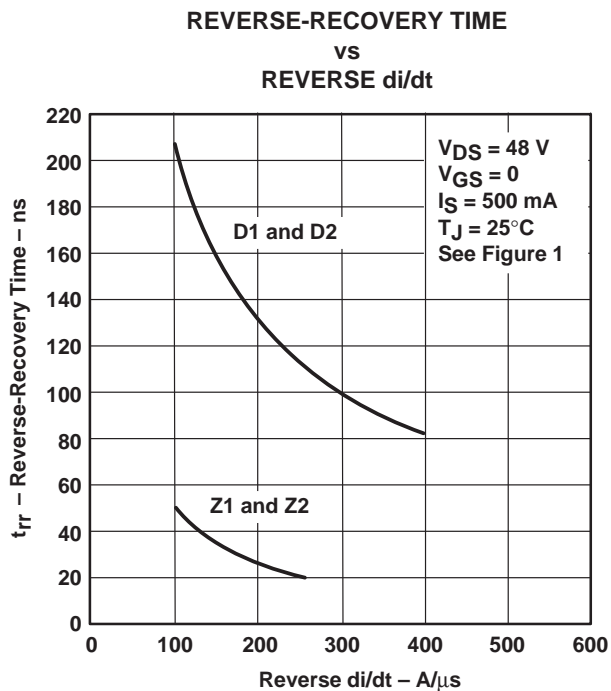
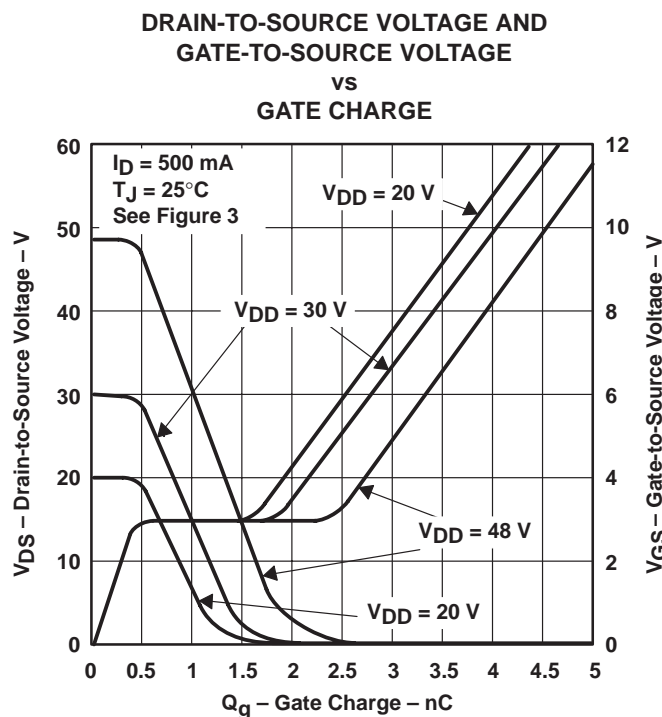
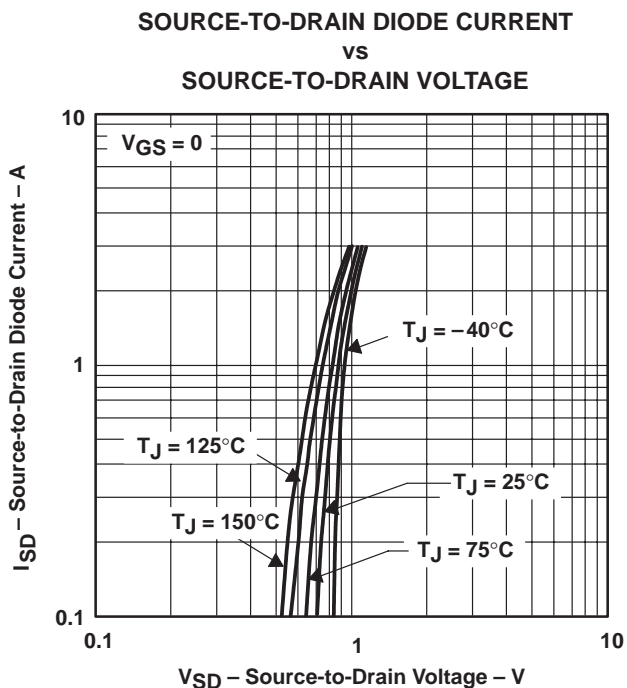
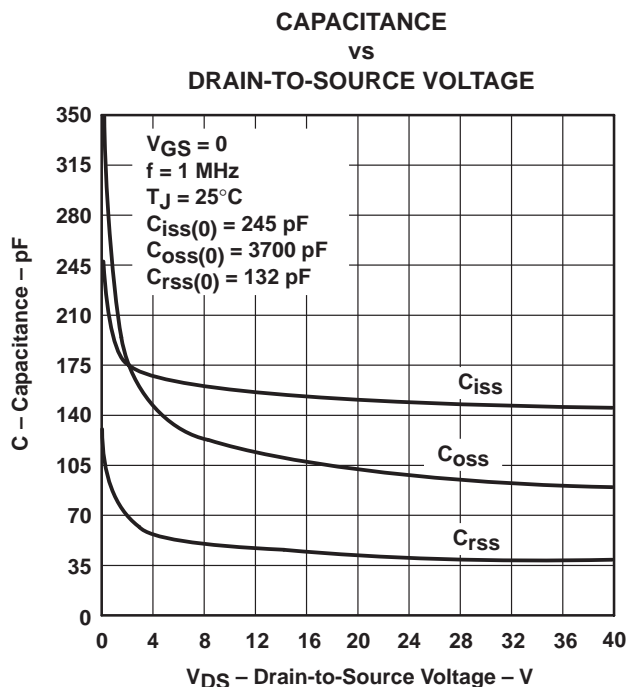
TPIC5223L

2-CHANNEL INDEPENDENT GATE-PROTECTED LOGIC-LEVEL

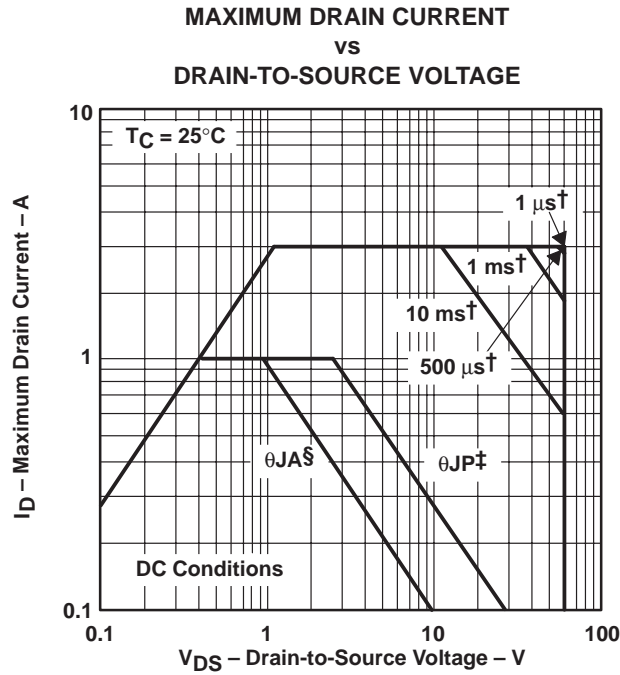
POWER DMOS ARRAY

SLIS043A – NOVEMBER 1994 – REVISED SEPTEMBER 1995

TYPICAL CHARACTERISTICS



THERMAL INFORMATION



† Less than 2% duty cycle

‡ Device mounted in intimate contact with infinite heatsink.

§ Device mounted on FR4 printed-circuit board with no heatsink.

Figure 15

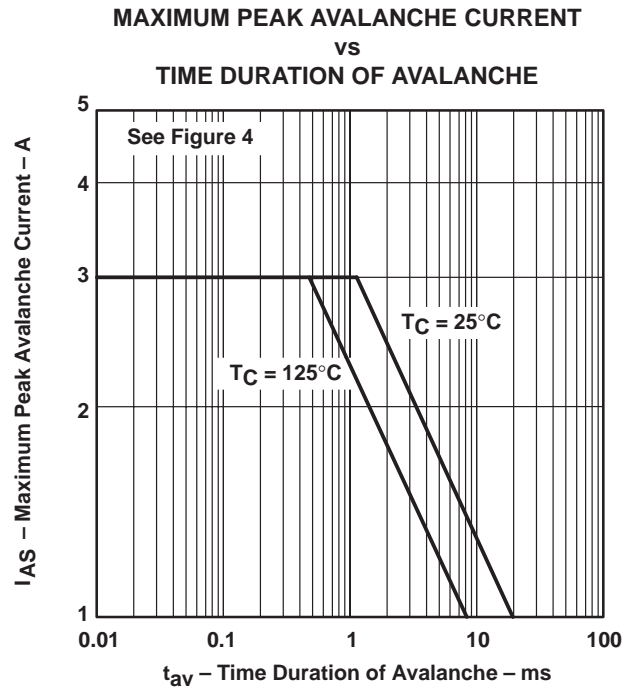


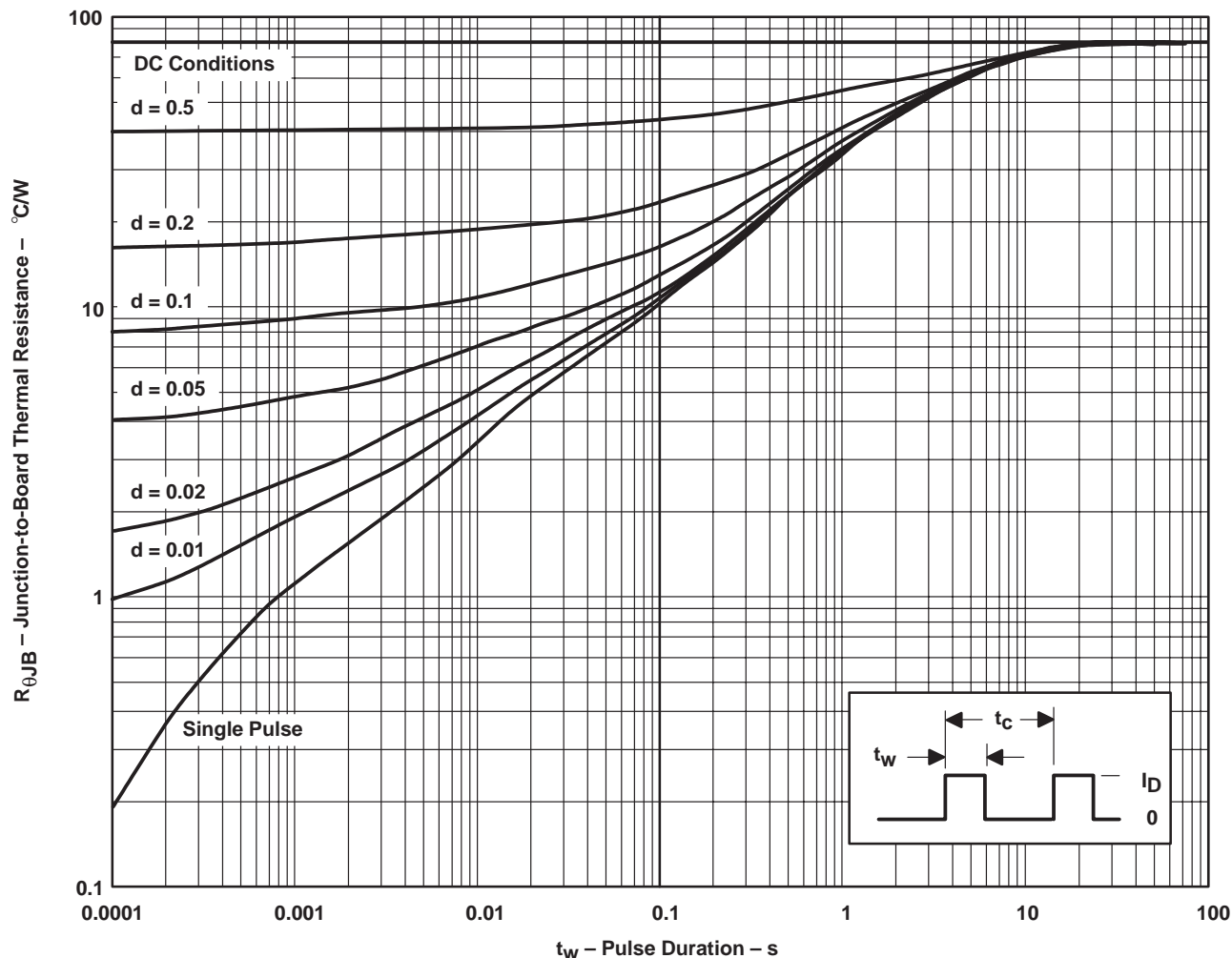
Figure 16

TPIC5223L
2-CHANNEL INDEPENDENT GATE-PROTECTED LOGIC-LEVEL
POWER DMOS ARRAY

SLIS043A – NOVEMBER 1994 – REVISED SEPTEMBER 1995

THERMAL INFORMATION

D PACKAGE†
JUNCTION-TO-BOARD THERMAL RESISTANCE
VS
PULSE DURATION



† Device mounted on 24 in², 4-layer FR4 printed-circuit board with no heatsink.

NOTE A: $Z_{\theta B}(t) = r(t) R_{\theta JB}$

t_W = pulse duration

t_C = cycle time

d = duty cycle = t_W/t_C

Figure 17

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